

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	"EP 744799"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/07 11:10
L2	201	("undoped silicate glass" or "USG") with "silicon dioxide"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/07 11:17
L3	6	("undoped silicate glass" or "USG") with ("silicon dioxide" or "silicon oxide") same ("SiOC" or "silicon oxycarbide")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/07 11:17
L5	0	@ad<="200300922" and ("si near1 o near1 C" or "si near1 o near1 c near1 n") same ("silicon oxide" or "silicon dioxide") same ("low k" or "low dielectric")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/07 11:47
L6	0	@ad<="200300922" and ("si near1 o near1 C" or "si near1 o near1 c near1 n") and ("silicon oxide" or "silicon dioxide") and ("low k" or "low dielectric")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/07 11:47
L7	0	@ad<="200300922" and ("si near1 o near1 C" or "si near1 o near1 c near1 n") same ("silicon oxide" or "silicon dioxide") same ("low k" or "low dielectric")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/07 11:47
L9	8	@ad<="200300922" and ("silicon oxide" or "silicon dioxide") same ("low k" or "low dielectric") same adhes\$3 same "silicon oxycarbide"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/07 11:50
L10	307	@ad<="200300922" and ("silicon oxide" or "silicon dioxide") same ("low k" or "low dielectric") same ("silicon oxycarbide" or "SiOC" or "SiCO")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/07 11:51
L11	147	@ad<="200300922" and ("silicon oxide" or "silicon dioxide") same ("low k" or "low dielectric") same ("silicon oxycarbide" or "SiOC" or "SiCO") and tungsten and copper	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/07 13:03
L12	1	@ad<="200300922" and ("silicon oxide" or "silicon dioxide") same ("low k" or "low dielectric") same ("silicon oxycarbide" or "SiOC" or "SiCO") and "silicon substrate" with germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/07 13:05

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L13	0	@ad<="20030922" and ("silicon oxide" or "silicon dioxide") same ("low k" or "low dielectric") same ("silicon oxycarbide" or "SiOC" or "SiCO") and "silicon substrate" with germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/07 13:05
L14	4	@ad<="20030922" and ("low k" or "low dielectric") same ("silicon oxycarbide" or "SiOC" or "SiCO") and "silicon substrate" with germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/07 13:27
L15	0	@ad<="20030922" and ("low k" or "low dielectric") same ("silicon oxycarbide" or "SiOC" or "SiCO") and "silicon substrate" with germanium with "SOI"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/07 13:06
L16	0	@ad<="20030922" and ("low k" or "low dielectric") same ("silicon oxycarbide" or "SiOC" or "SiCO") and "substrate" with silicon with germanium with "SOI"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/07 13:07
L17	0	@ad<="20030922" and ("silicon oxycarbide" or "SiOC" or "SiCO") and "substrate" with silicon with germanium with "SOI"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/07 13:29
L18	4	("6908847").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/07 13:27
L19	144	@ad<="20030922" and "low dielectric" with "SiOC"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/07 13:29
L20	168	@ad<="20030922" and "dielectric constant" with "SiOC"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/07 13:33
L21	117	@ad<="20030922" and "low dielectric constant" with "SiOC"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/07 13:45
L22	0	@ad<="20030922" and "low dielectric constant" with "SiOC" and gate with "nickel silicide"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/07 13:47

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L23	0	@ad<="20030922" and "low dielectric" with "SiOC" and gate with "nickel silicide"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/07 13:47
L24	0	@ad<="20030922" and "low dielectric" with "SiOC" and (gate or conductor) with "nickel silicide"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/07 13:48
L25	326	@ad<="20030922" and (gate or conductor) with "nickel silicide"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/07 13:48
S1	1705	@ad<="20020607" and (257/773). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 11:42
S2	4488	@ad<="20020607" and (438/622-624).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 09:09
S3	557	@ad<="20020607" and (438/629). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 11:42
S4	1623	@ad<="20020607" and (438/637). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 11:42
S5	545	@ad<="20020607" and (438/631). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 11:42
S9	23	@ad<="20020607" and 'interconnection' and 'SiOC' same 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:34
S10	1	@ad<="20020607" and 'dielectric' same 'SiOC' same 'undoped silicate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/10 10:50
S11	28	@ad<="20020607" and 'dielectric' same 'SiOC' same 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 09:57

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S12	2	@ad<="20020607" and 'dielectric' same 'SiOC' same 'SiC' same 'PSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/10 12:12
S13	1	@ad<="20020607" and 'dielectric' same 'SiOC' same 'SiC' same 'USG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/10 12:13
S15	26	@ad<="20020607" and 'interconnection' and 'SiOC' same 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/26 17:39
S16	2	@ad<="20020607" and 'interconnection' and 'SiOC' and 'USG' and 'SiN'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/26 17:45
S17	15	@ad<="20020607" and 'interconnection' and 'SiOC' same 'SiC' and 'SiN'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/26 17:45
S18	28	@ad<="20020607" and 'low k' same 'silicon oxide' same 'SiN'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/09 14:34
S19	969	@ad<="20020607" and (257/750).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 11:43
S20	2856	@ad<="20020607" and (257/758-760).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 11:44
S21	1737	@ad<="20020607" and (257/773).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 11:45
S22	4552	@ad<="20020607" and (438/622-624).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 11:47
S23	564	@ad<="20020607" and (438/629).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 11:47

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S24	1664	@ad<="20020607" and (438/637). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 11:49
S25	548	@ad<="20020607" and (438/631). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 11:49
S26	2	"20030227087"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/09 13:41
S27	86	@ad<="20020607" and 'hard mask' same 'SiN' with 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 12:22
S28	39	@ad<="20020607" and 'hard mask' same 'SiN' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/09 14:36
S29	18	@ad<="20020607" and 'low k' same 'hard mask' same 'SiN' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/09 14:36
S30	2	@ad<="20020607" and 'MSQ' same 'hard mask' same 'SiN' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:43
S31	5	@ad<="20020607" and 'MSQ' same 'SiN' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/09 14:59
S32	19	@ad<="20020607" and 'hard mask' same 'SiC' with 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 12:23
S33	2	@ad<="20020607" and 'hard mask' same 'SiC' with 'TEOS'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 13:41
S34	17	@ad<="20020607" and 'etch stop' with 'SiC' with "'SiO.sub.2'"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 13:42

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S35	2	@ad<="20020607" and 'MSQ' same 'etch stop' with 'SiC' with "SiO.sub.2"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 13:42
S36	4	"6677183"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 15:38
S37	649	@ad<="20020607" and 'interconnection' same 'tungsten' with 'copper' same 'low k' same 'etch stop' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:25
S38	31	@ad<="20020607" and 'interconnection' same 'tungsten plug' with 'copper' same 'low k' same 'etch stop' with 'SiC' same 'USG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:30
S39	90	@ad<="20020607" and 'tungsten copper' same 'interconnection'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:32
S41	17	@ad<="20020607" and 'tungsten copper' same 'interconnection' and 'etch stop'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:32
S43	7	@ad<="20020607" and 'interconnection' and 'USG' and 'SiC' and 'low k'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:35
S44	12	@ad<="20030922" and 'interconnection' and 'USG' and 'SiC' and 'low k'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:35
S45	1	"6312793".PN.	USPAT	OR	OFF	2004/10/31 08:39
S46	1	"6303523".PN.	USPAT	OR	OFF	2004/10/31 08:40
S47	1	"6238751".PN.	USPAT	OR	OFF	2004/10/31 08:40
S48	1	"6147009".PN.	USPAT	OR	OFF	2004/10/31 08:40
S49	1	"6072227".PN.	USPAT	OR	OFF	2004/10/31 08:40
S50	1	"6054379".PN.	USPAT	OR	OFF	2004/10/31 08:40
S51	1	"6001747".PN.	USPAT	OR	OFF	2004/10/31 08:41
S52	1	"5989998".PN.	USPAT	OR	OFF	2004/10/31 08:41

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S53	2	@ad<="20020607" and 'USG' same 'hard mask' same 'low dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:46
S54	270	@ad<="20020607" and 'dielectric' same 'hard mask' same 'low dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:58
S55	24	@ad<="20020607" and 'interconnection' same 'dielectric' same 'hard mask' same 'low dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:53
S56	4	((("6465867") or ("6016000")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/31 08:55
S57	2	"20010045651"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:55
S58	190	@ad<="20020607" and 'dielectric' same 'SiC' same 'low dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:59
S59	56	@ad<="20020607" and 'dielectric' same 'SiC' same 'low dielectric' same 'barrier'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 09:43
S60	34	@ad<="20020607" and 'dielectric' same 'SiC' same 'low-k' same 'barrier'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:59
S61	2447	@ad<="20030922" and (257/750-752).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 09:03
S62	1757	@ad<="20030922" and (257/753-756).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 09:05

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S63	3767	@ad<="20030922" and (257/757-760).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 09:06
S64	1886	@ad<="20030922" and (257/773).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 09:07
S65	126	@ad<="20030922" and 'dielectric constant' with 'SiOC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 09:15
S66	7	@ad<="20030922" and 'conductive plug' with 'Cu' with 'W' with 'silicide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 09:31
S67	138	@ad<="20030922" and 'conductive' with 'Cu' with 'W' with 'silicide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 09:18
S68	1	@ad<="20030922" and 'interconnect' same 'conductive' with 'Cu' with 'W' with 'silicide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 09:19
S69	12	@ad<="20030922" and 'interconnection' same 'conductive' with 'Cu' with 'W' with 'silicide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 09:19
S70	36	@ad<="20030922" and 'interconnection' same 'substrate' with 'Silicon' with 'silicon germanium'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 09:32
S77	20	@ad<="20030922" and 'etch stop' same 'SiOC' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 11:26
S78	3	@ad<="20030922" and 'etch stop' same 'SiCON' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 11:05
S79	1	@ad<="20030922" and 'etch stop' same 'SiCON' same 'SiC' same 'SiCO'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 11:05

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S80	9	@ad<="20030922" and 'etch stop' same 'SiCO' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 09:42
S81	1	@ad<="20030922" and 'etch stop' same 'SiOCN' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 11:28
S82	2	@ad<="20030922" and 'hard mask' same 'SiOCN' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 11:30
S83	2	@ad<="20030922" and 'hard mask' same 'SiCON' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 09:42
S84	31	@ad<="20030922" and 'hard mask' same ('SiCO' or 'SiOC') with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 09:43
S85	8	(("6140224") or ("6339025") or ("5559367") or ("6147007")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 11:49
S86	2	("6147009").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 11:49
S87	2	@ad<="20030922" and 'substrate' and 'interconnection' and 'SiOC' and 'USG' and 'low k' and 'copper'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:11
S91	3	@ad<="20030922" and 'etch stop' with 'SiCO' and 'USG' and 'low k' and 'copper'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 13:13
S93	109	@ad<="20030922" and 'dielectric constant' with 'Black Diamond'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 13:13

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S94	4	((("5811357") or ("4172158")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/27 09:27
S95	1	"6440840".PN.	USPAT; USOCR	OR	ON	2005/09/27 09:31
S96	1	"6037664".PN.	USPAT; USOCR	OR	ON	2005/09/27 09:31
S97	1	@ad<="20030922" and 'etch stop' same 'Si' near1 'C' near1 'O' near1 'N'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 09:38
S98	1	@ad<="20030922" and 'etch stop' same 'SiOCN' with 'SiON'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 09:38
S99	1	@ad<="20030922" and 'etch stop' same 'SiOCN' same 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 09:39
S10 0	1	@ad<="20030922" and 'etch stop' same 'SiOCN' same 'SiN'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 09:39
S10 1	1	@ad<="20030922" and 'etch stop' same 'Si' near1 'O' near1 'C' near1 'N'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 09:40
S10 2	9	@ad<="20030922" and 'etch stop' same 'SiCO' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 09:46
S10 3	2	@ad<="20030922" and 'hard mask' same 'SiCON' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 09:42
S10 4	32	@ad<="20030922" and 'hard mask' same ('SiCO' or 'SiOC') with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 09:43

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S10 5	60	@ad<="20020607" and 'dielectric' same 'SiC' same 'low dielectric' same 'barrier'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 09:43
S10 6	28	@ad<="20020607" and 'dielectric' same 'low dielectric' same 'barrier' and ('SiOCN' or 'SiCON' or 'SiCNO')	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 09:44
S10 7	98	'etch stop' and 'SiCON' or 'SiONC' or 'SiOCN'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 09:48
S10 8	98	'etch stop' same 'SiCON' or 'SiONC' or 'SiOCN'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 09:49
S10 9	95	'etch stop' with 'SiCON' or 'SiONC' or 'SiOCN'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 09:49
S11 0	95	@ad<="20030922" and 'etch stop' with 'SiCON' or 'SiONC' or 'SiOCN'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 12:09
S11 1	85	@ad<="20030922" and 'hard mask' with 'SiCON' or 'SiONC' or 'SiOCN'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 12:11
S11 2	2	@ad<="20030922" and 'hard mask' with ('SiCON' or 'SiONC' or 'SiOCN')	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 12:11
S11 3	2	@ad<="200300922" and ("SiOC" or "SiOCN" or "SiCON") and "USG" and (plug with tungsten) and "low k"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 14:37
S11 4	8	@ad<="200300922" and ("SiOC" or "SiOCN" or "SiCON") and "USG" and plug and "low k"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 14:23
S11 5	22	@ad<="200300922" and ("SiOC" or "SiCO" or "SiOCN" or "SiCON") and ("USG" or "undoped silicate glass") and plug and "low dielectric"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 14:53

EAST Search History

S11 6	0	@ad<="200300922" and ("SiOC" or "SiCO" or "SiOCN" or "SiCON") near ("USG" or "undoped silicate glass")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 14:53
S11 7	32	@ad<="200300922" and ("SiOC" or "SiCO" or "SiOCN" or "SiCON") same ("USG" or "undoped silicate glass")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 15:27
S11 8	367	@ad<="200300922" and "silicon oxide" with ("USG" or "undoped silicate glass")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 15:33
S12 0	346	@ad<="200300922" and "silicon oxide" with "USG"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 15:29
S12 1	7	@ad<="200300922" and ("USG" or "undoped silicate glass") same ("carbon-doped silicon oxide" or Si near1 C near1 O)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 15:53
S12 4	200	@ad<="200300922" and "USG" with "adhesive" with (si near1 o near1 C) or (si near1 o near1 c near1 n)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 15:51
S12 5	17	@ad<="200300922" and "adhesive" with (Si near1 O near1 C)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 15:52
S12 6	37	@ad<="200300922" and ("USG" or "undoped silicate glass") and ("carbon-doped silicon oxide" or Si near1 C near1 O)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 15:59
S12 7	1	@ad<="200300922" and "SOG" with ("USG" or "undoped silicate glass") and ("carbon-doped silicon oxide" or Si near1 C near1 O)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 15:56
S12 8	112	@ad<="200300922" and ("USG" or "undoped silicate glass" or "silicon oxycarbide") and ("carbon-doped silicon oxide" or Si near1 C near1 O)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 15:59